

## InGaAs and Silicon Integrated Photo Detectors

### Features:

- Integrated InGaAs and Silicon photodetector chips
- Cover 400~1700nm response wavelength
- Standard TO5 package

### Applications:

- Optical measurement equipment
- Optical communication
- Analytical equipment, etc.



### Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE		UNIT
		Silicon	InGaAs	
Operating Temperature	$T_{op}$	-40~+85	-40~+85	°C
Storage Temperature	$T_{stg}$	-40 ~ +125	-40 ~ +125	°C
Reverse Voltage	$V_r$	100	50	V
Reverse Current	$I_r$	10	10	μA

SPECIFICATIONS	Testing condition	GCPD-12P12		Unit
		Silicon	InGaAs	
Sensitive Area	-	∅2	∅1	mm
Responsibility	$V_r=15V, \lambda =530nm$	$\geq 0.2$	-	A/W
	$V_r=15V, \lambda =1060nm$	$\geq 0.3$	-	A/W
Responsibility	$V_r=5V, \lambda =1310nm$	-	$\geq 0.5$	A/W
	$V_r=5V, \lambda =1550nm$	-	$\geq 0.5$	A/W
Response Spectrum	-	400~1700		nm
Dark Current (Typical)	$V_r=15V$	$\leq 40$	-	nA
	$V_r=5V$	-	$\leq 10$	nA
Rise / Fall Time	$V_r=15V, R=50\Omega$	10	-	ns
	$V_r=5V, R=50\Omega$	-	10	ns
Saturation Power(Typical)	$V_r=5V$	$\geq 2$	2	mW
Package Style	-	TO5		-